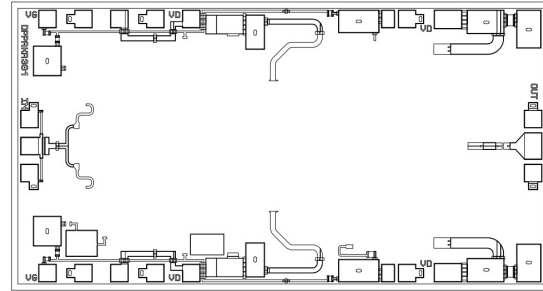


Performance

- Frequency: 33-37GHz
- Psat: 30dBm@6V, 29dBm@5V
- PAE: 30%
- Power Gain: 18dB
- Linear Gain: 20dB
- VSWRin: 2
- Bias: $V_g = -0.8V$, $V_d = 5\sim 6V$
- Size: 3.0*1.6mm*0.05mm
- Technology: 0.15um pHEMT

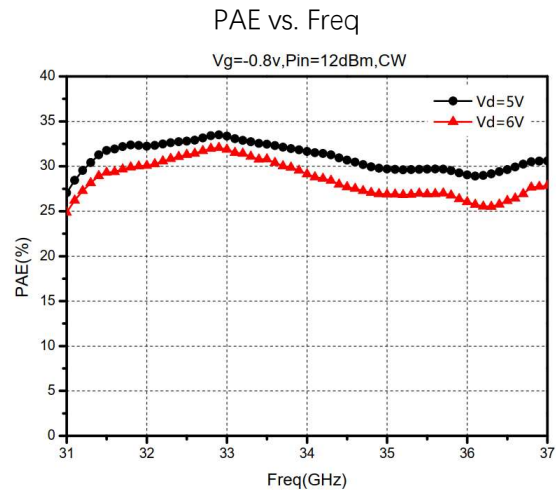
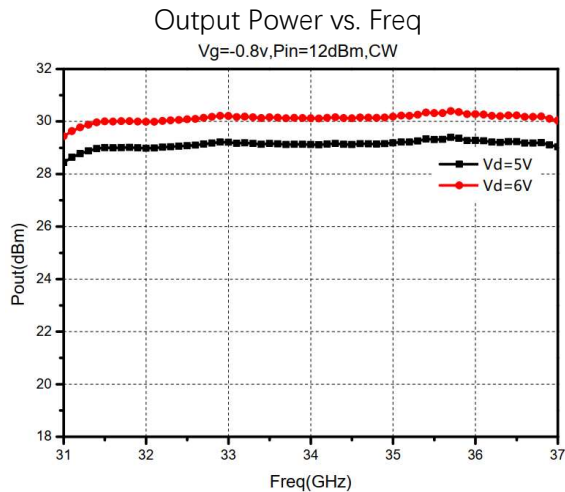
Function Diagram



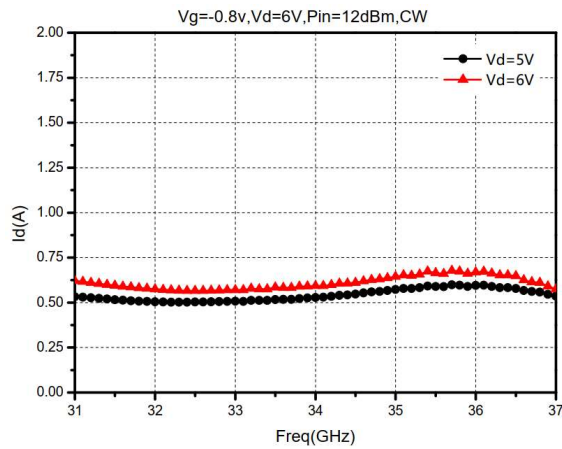
Electrical Specifications ($T_A = 25^\circ C$, 33-37GHz, $V_g = -0.8V$, $V_d = 5\sim 6V$)

Symbol	Parameter	Min	Typical	Max	Unit
Psat	Saturated Output Power	29	30	-	dBm
PAE	Power Added Efficiency	30	32	-	%
Gp	Saturated Power Gain	-	18	-	dB
ΔG_p	Power Gain Flatness	-	± 0.5	-	dB
Glin	Linear Gain	-	20	-	dB
VSWRin	Input VSWR	-	2	-	-

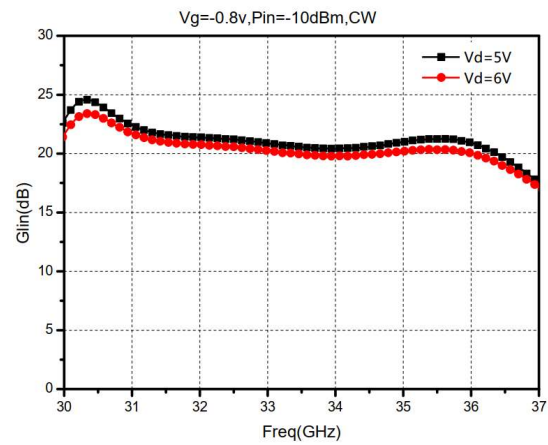
Test Curves



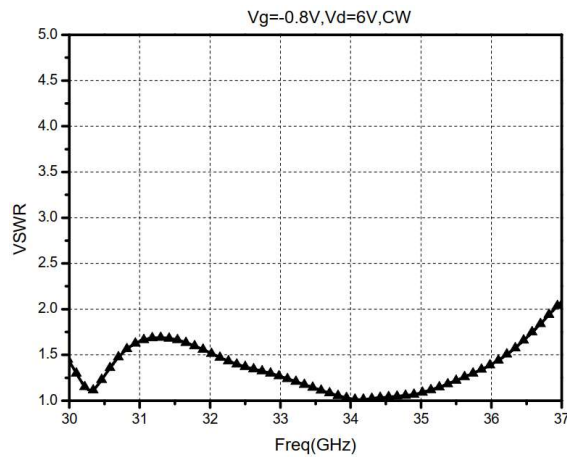
Current of Drain



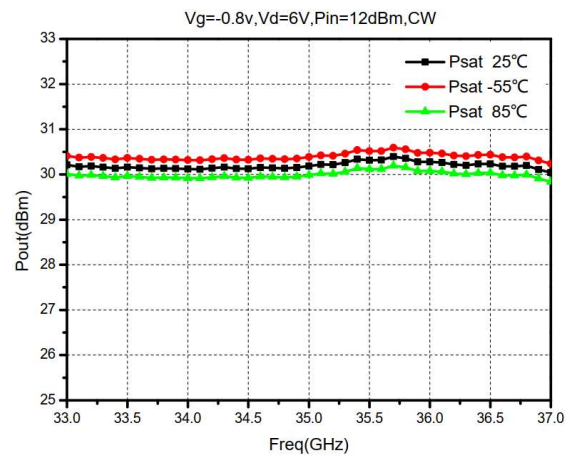
Linear Gain



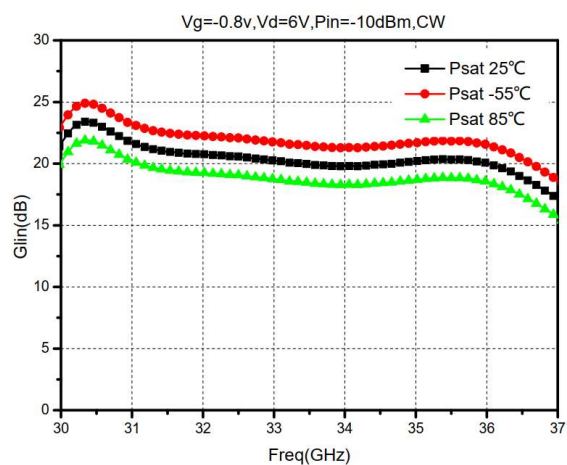
VSWR vs. Freq



Output Power vs. Freq



Linear Gain vs. Freq

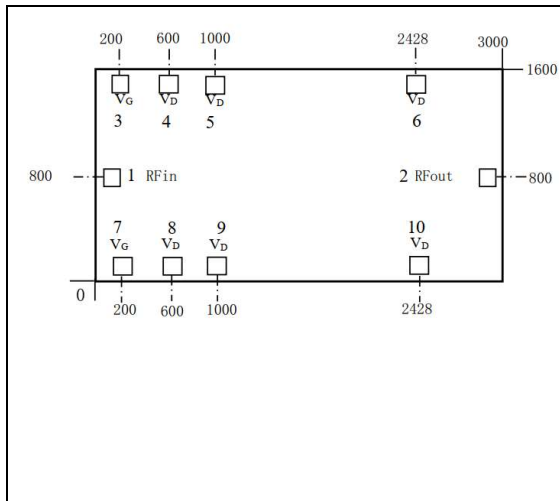


Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Bias Voltage	+7V	
I _d	Drain Bias Current	5A	
V _g	Gate Bias Voltage	-2V	
I _g	Gate Bias Current	100mA	
P _d	Power Dissipation	30W	
P _{in}	Input CW Power	30 dBm	
T _{ch}	Channel Temperature	150°C	
T _m	Mounting Temperature	300°C	30s, N ₂ Protection
T _{stg}	Storage Temperature	-55~150°C	

Exceeding any one or combination of these limits may cause permanent damage.

Outline Size



Assembly Drawing

